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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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ST2001FX

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

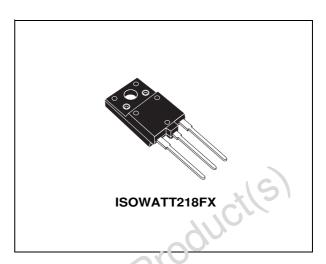
- NEW SERIES, ENHANCED PERFORMANCE
- FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING
- HIGH VOLTAGE CAPABILITY
- HIGH SWITCHING SPEED
- TIGTHER hfe CONTROL
- IMPROVED RUGGEDNESS

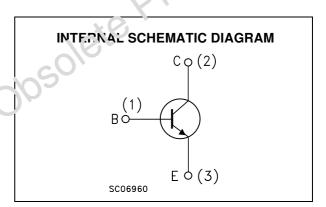
APPLICATIONS:

 HORIZONTAL DEFLECTION FOR COLOR TVS OVER 21 INCHES AND 15 INCHES MONITORS

DESCRIPTION

The device is manufactured using Diffused Collector technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
VCPO	Collector-Base Voltage (I _E = 0)	1500	V
1/SE O	Collector-Emitter Voltage (I _B = 0)	600	٧
VEBO	Emitter-Base Voltage (I _C = 0)	7	٧
Ic	Collector Current	10	Α
I _{CM}	Collector Peak Current (t _p < 5 ms)	20	Α
I _B	Base Current	7	Α
P _{tot}	Total Dissipation at T _c = 25 °C	63	W
V _{ins}	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	2500	V
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

October 2003 1/7

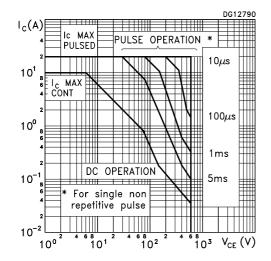
THERMAL DATA

R _{thj-case} Therr	mal Resistance Junction-case	Max	2	°C/W
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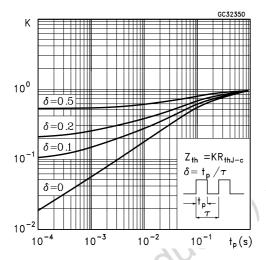
ELECTRICAL CHARACTERISTICS ($T_j = 25$ °C unless otherwise specified)

I _{CES}	Collector Cut-off		onditions	Min.	Тур.	Max.	Un
	Current (V _{BE} = 0)	V _{CE} = 1500 V V _{CE} = 1500 V	T _j = 125 °C			1 2	m/ m/
	Emitter Cut-off Current (I _C = 0)	V _{EB} = 7 V				1	m
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA		600			٧
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 5 A	I _B = 1.25 A			1.5	٧
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 5 A	I _B = 1.25 A			1.2	١
h _{FE} *	DC Current Gain	I _C = 6 A	V _{CE} = 1 V V _{CE} = 5 V	5	4.5	9	5
t _s	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 5 \text{ A}$ $I_{Bon (END)} = 850 \text{ mA}$ $L_{BB(off)} = 2 \mu H$	$V_{BB(off)} = -2.5 \text{ V}$ $f_h = 64 \text{ KHz}$ (See Figure 1)		2.6 0.2	3 0.4	μ
		*(5)					
		(C)					
	·od/), -					
	.e.Prodi)					
·0/	sie Prodi						
osol	Fall Time e duration = 300 μs, duty cycle						

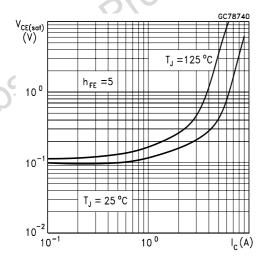
Safe Operating Area



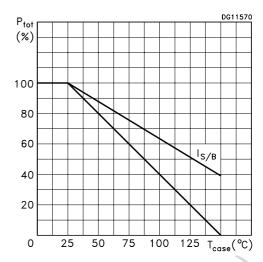
Thermal Impedance



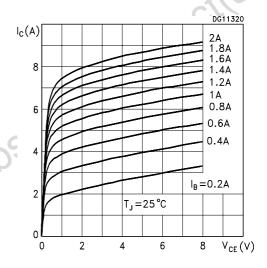
Collector-Emitter Saturation Voltage



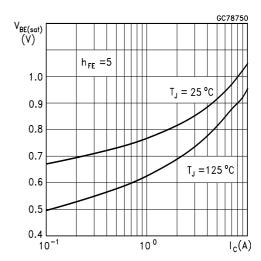
Derating Curve



Output Characteristics

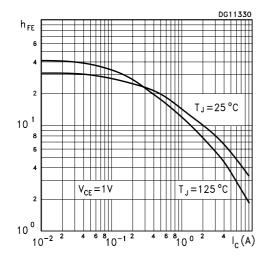


Base-Emitter Saturation Voltage

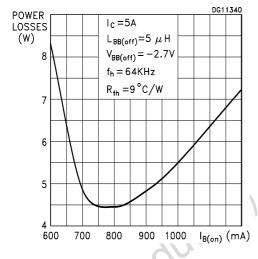


ST2001FX

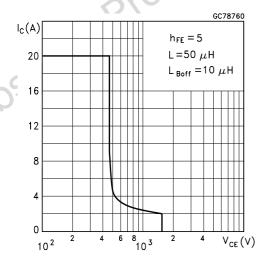
DC Current Gain



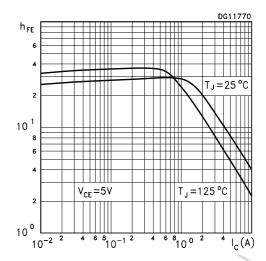
Power Losses



Reverse Biased Safe Operating Area



DC Current Gain



Inductive Load Switchin Times

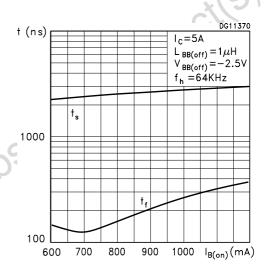
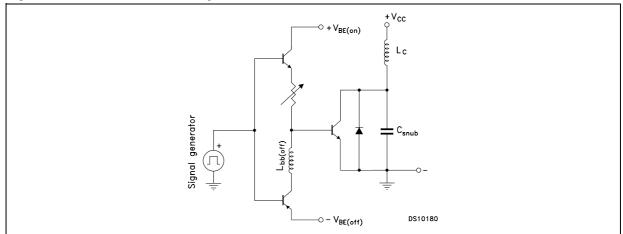


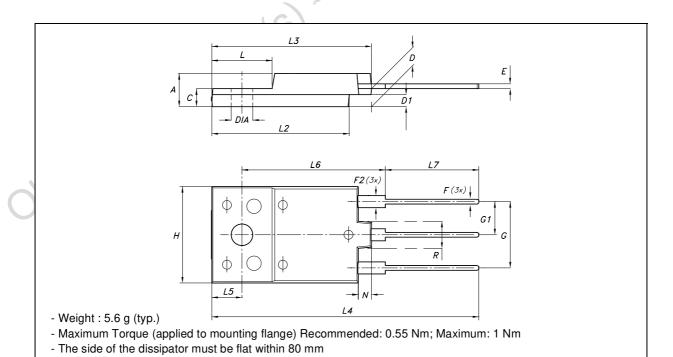
Figure 1: Inductive Load Switching Test Circuit



Obsolete Product(s)

ISOWATT218FX MECHANICAL DATA

DIM.	mm.			inch			
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	5.30		5.70	0.209		0.224	
С	2.80		3.20	0.110		0.126	
D	3.10		3.50	0.122		0.138	
D1	1.80		2.20	0.071		0.087	
Е	0.80		1.10	0.031		0.043	
F	0.65		0.95	0.026		0.037	
F2	1.80		2.20	0.071		0.087	
G	10.30		11.50	0.406		0.453	
G1		5.45			0.215		
Н	15.30		15.70	0.602		0.618	
L	9.80		10.20	0.386		0.402	
L2	22.80		23.20	0.898		0.913	
L3	26.30		26.70	1.035	AU	1.051	
L4	43.20		44.40	1.701	~400	1.748	
L5	4.30		4.70	0.169		0.185	
L6	24.30		24.70	0.957		0.972	
L7	14.60		15.00	0.575		0.591	
N	1.80		2.20	0.071		0.087	
R	3.80		4.20	0.150		0.165	
DIA	3.40		3.80	0.134		0.150	



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